# **HD74AC539**

Dual 1-of-4 Decoder with 3-State Output

# **HITACHI**

#### **Description**

The HD74AC539 contains two inpedendent decoders. Each accepts two Address  $(A_0, A_1)$  input signals and decodes them to select one of four mutually exclusive outputs. A polarity control input (P) determines whether the outputs are active HIGH (P = L) or active LOW (P = H). An active LOW input Enable  $(\overline{E})$  is available for data demultiplexing; data is routed to the selected output in non-inverted form in the active LOW mode or in inverted form in the active HIGH mode. A HIGH signal on the active LOW Output Enable  $(\overline{OE})$  input forces the 3-state outputs to the high impedance state.

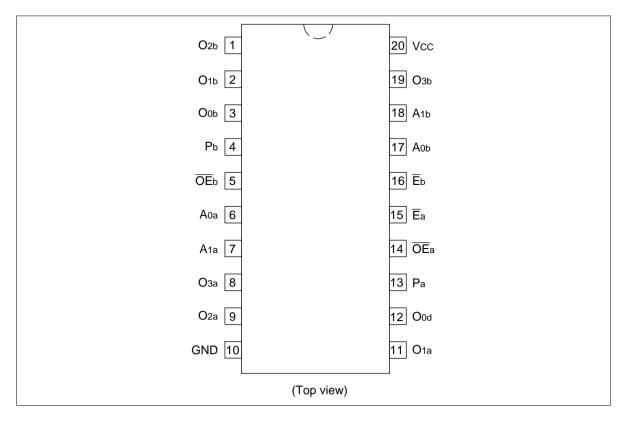
#### **Feature**

Outputs Source/Sink 24 mA

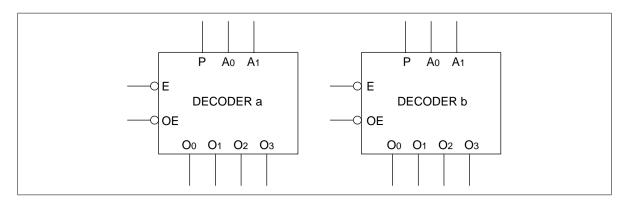


# **HD74AC539**

## **Pin Arrangement**



## Logic Symbol



## Pin Names

$A_{0a}$ to $A_{1a}$	Side A Address Inputs
$A_{0b}$ to $A_{1b}$	Side B Address Inputs
$\overline{E}_a - \overline{E}_b$	Enable Inputs (Active LOW)
$\overline{OE}_a$ , $\overline{OE}_b$	Output Enable Inputs (Active LOW)
$P_a, P_b$	Polarity Control Inputs
$O_{0a}$ to $O_{3a}$	Side A 3-State Outputs
$O_{0b}$ to $O_{3b}$	Side B 3-State Outputs

#### **Truth Table**

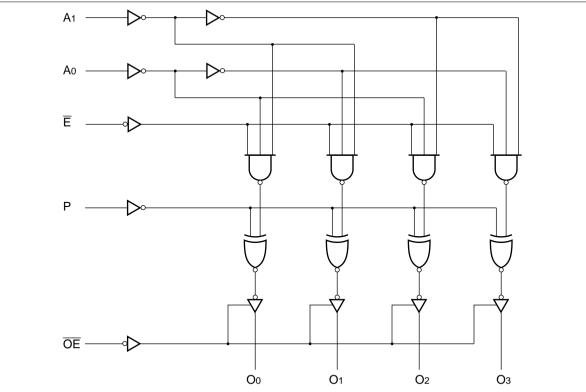
	Inputs				Outpu	uts			
Function	OE	Ē	<b>A</b> <sub>1</sub>	A <sub>0</sub>	O <sub>0</sub>	<b>O</b> <sub>1</sub>	O <sub>2</sub>	O <sub>3</sub>	
High impedance	Н	Х	Х	Х	Z	Z	Z	Z	
Disable	L	Н	Х	Х	$O_n = F$	)			
Active HIGH output	L	L	L	L	Н	L	L	L	
(P = L)	L	L	L	Н	L	Н	L	L	
	L	L	Н	L	L	L	Н	L	
	L	L	Н	Н	L	L	L	Н	
Active LOW output	L	L	L	L	L	Н	Н	Н	
(P = H)	L	L	L	Н	Н	L	Н	Н	
	L	L	Н	L	Н	Н	L	Н	
	L	L	Н	Н	Н	Н	Н	L	

H: High Voltage Level
L: Low Voltage Level

X : ImmaterialZ : High Impedance

# **HD74AC539**

## **Logic Diagram** (one half shown)



Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

## **DC Characteristics** (unless otherwise specified)

Item	Symbol	Max	Unit	Condition
Maximum quiescent supply current	I <sub>cc</sub>	80	μΑ	$V_{IN} = V_{CC}$ or ground, $V_{CC} = 5.5 \text{ V}$ , Ta = Worst case
Maximum quiescent supply current	I <sub>cc</sub>	8.0	μΑ	$V_{IN} = V_{CC}$ or ground, $V_{CC} = 5.5 \text{ V}$ , $Ta = 25^{\circ}\text{C}$

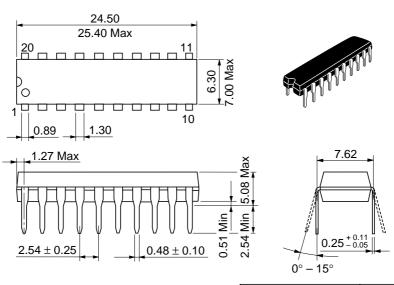
## **AC Characteristics: HD74AC539**

			Ta = +25°C C <sub>L</sub> = 50 pF		Ta = $-40^{\circ}$ C to $+85^{\circ}$ C C <sub>L</sub> = 50 pF			
Item	Symbol	V <sub>cc</sub> (V)*1	Min	Тур	Max	Min	Max	Unit
Propagation delay	t <sub>PLH</sub>	3.3	1.0	_	15.0	1.0	18.0	ns
$A_n$ to $O_n$		5.0	1.0	_	10.0	1.0	12.0	
Propagation delay	t <sub>PHL</sub>	3.3	1.0	_	15.0	1.0	18.0	ns
$A_n$ to $O_n$		5.0	1.0	_	10.0	1.0	12.0	
Propagation delay	t <sub>PLH</sub>	3.3	1.0	_	14.5	1.0	16.5	ns
$\overline{E}$ to $O_n$		5.0	1.0	_	9.5	1.0	11.0	<del></del>
Propagation delay	t <sub>PHL</sub>	3.3	1.0	_	13.5	1.0	15.5	ns
$\overline{E}$ to $O_{n}$		5.0	1.0	_	9.0	1.0	11.5	<del></del>
Propagation delay	t <sub>PLH</sub>	3.3	1.0	_	16.0	1.0	19.0	ns
P to O <sub>n</sub>		5.0	1.0	_	11.5	1.0	12.5	<del></del>
Propagation delay	t <sub>PHL</sub>	3.3	1.0	_	16.0	1.0	19.0	ns
P to O <sub>n</sub>		5.0	1.0	_	11.5	1.0	12.5	<del></del>
Propagation delay	t <sub>zH</sub>	3.3	1.0	_	10.0	1.0	11.5	ns
$\overline{OE}$ to $O_{\scriptscriptstylen}$		5.0	1.0	_	8.0	1.0	9.0	<del></del>
Propagation delay	t <sub>zL</sub>	3.3	1.0	_	9.5	1.0	11.0	ns
$\overline{OE}$ to $O_{n}$		5.0	1.0	_	7.5	1.0	8.5	<del></del>
Propagation delay	t <sub>HZ</sub>	3.3	1.0	_	11.5	1.0	13.0	ns
$\overline{OE}$ to $O_{\scriptscriptstylen}$		5.0	1.0	_	9.5	1.0	10.5	_
Propagation delay	t <sub>LZ</sub>	3.3	1.0	_	10.5	1.0	12.0	ns
OE to O <sub>n</sub>		5.0	1.0	_	8.5	1.0	9.5	_

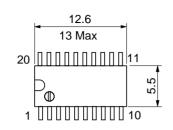
Note: 1. Voltage Range 3.3 is  $3.3 \text{ V} \pm 0.3 \text{ V}$ Voltage Range 5.0 is  $5.0 \text{ V} \pm 0.5 \text{ V}$ 

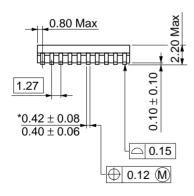
# Capacitance

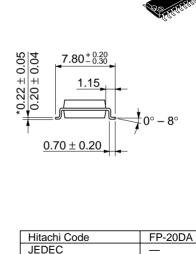
Item	Symbol	Тур	Unit	Condition	
Input capacitance	C <sub>IN</sub>	4.5	pF	$V_{cc} = 5.5 \text{ V}$	
Power dissipation capacitance	$C_{PD}$	60	pF	$V_{CC} = 5.0 \text{ V}$	



Hitachi Code	DP-20N
JEDEC	_
EIAJ	Conforms
Weight (reference value)	1.26 g







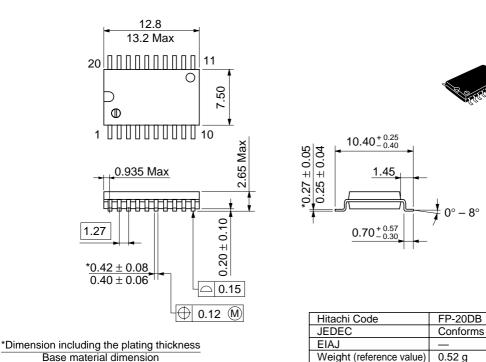
Weight (reference value)

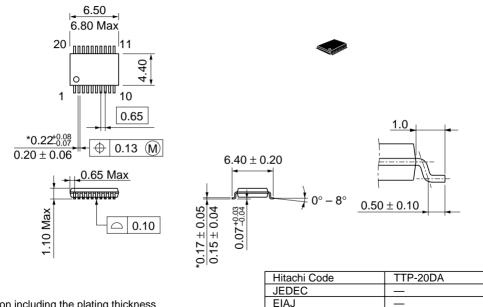
Conforms

0.31 g

EIAJ

\*Dimension including the plating thickness
Base material dimension





Weight (reference value)

0.07 g

\*Dimension including the plating thickness
Base material dimension

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# HTACHI

#### Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group Dornacher Stra§e 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park

Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000

Fax: <44> (1628) 778322

Lower Cookham Road

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666

Fax: <886> (2) 2718-8180

7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

Hitachi Asia (Hong Kong) Ltd.

Group III (Electronic Components)

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